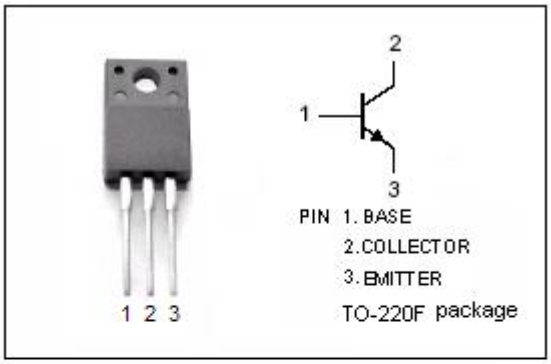
isc Silicon NPN Power Transistor — 2SC4327

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 35V(Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 0.5V(Max)@ (I_C= 5A, I_B= 0.3A)
- Complement to Type 2SA1643
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

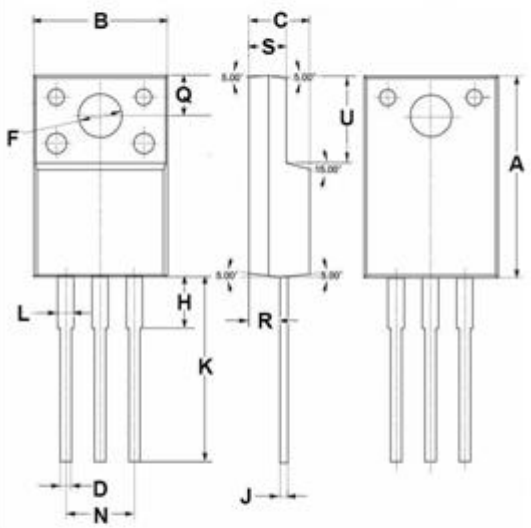


APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	7	A
P_C	Collector Power Dissipation @T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 25mA; I_B= 0	35			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.3A			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 0.3A			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 50V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			10	μA
h_{FE}	DC Current Gain	I_C= 5A; V_{CE}= 2V	50			
f_T	Current-Gain—Bandwidth Product	I_E= -1A; V_{CE}= 12V		115		MHz